优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

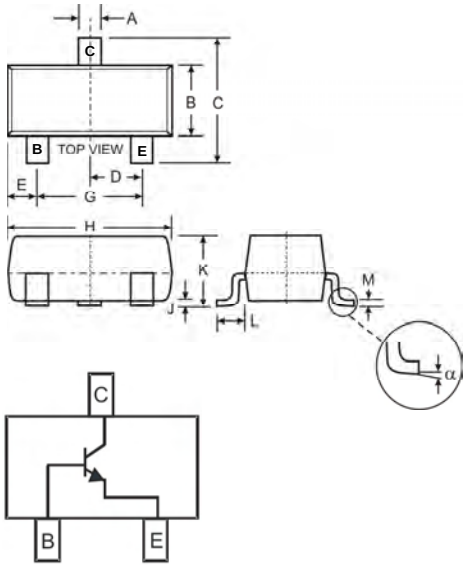
企业QQ二维码

Features

- Designed for VHF/UHF Amplifier Applications and High Output VHF Oscillators
- High Current Gain Bandwidth Product
- Ideal for Mixer and RF Amplifier Applications with collector currents in the 100μA - 30 mA Range

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: K3H, K3Y; See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	**Min**	**Max**
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current - Continuous (Note 1)	I_C	50	mA
Power Dissipation (Note 1)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	25	—	V	I_C = 1mA, I_B = 0
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	30	—	V	I_C = 100μA, I_E = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	3.0	—	V	I_E = 10μA, I_C = 0
Collector Cutoff Current	I_{CBO}	—	100	nA	V_{CB} = 25V, I_E = 0
Emitter Cutoff Current	I_{EBO}	—	100	nA	V_{EB} = 2V, I_C = 0
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	60	—	—	I_C = 4mA, V_{CE} = 10.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.5	V	I_C = 4mA, I_B = 400μA
Base-Emitter On Voltage	$V_{BE(SAT)}$	—	0.95	V	I_C = 4mA, V_{CE} = 10.0V
SMALL SIGNAL CHARACTERISTICS					
Current Gain-Bandwidth Product	f_T	650	—	MHz	V_{CE} = 10V, f = 100MHz, I_C = 4mA
Collector-Base Capacitance	C_{CB}	—	0.7	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Collector-Base Feedback Capacitance	C_{RB}	—	0.65	pF	V_{CB} = 10V, f = 1.0MHz, I_E = 0
Collector-Base Time Constant	Rb'Cc	—	9	ps	V_{CB} = 10V, f = 31.8MHz, I_C = 4mA

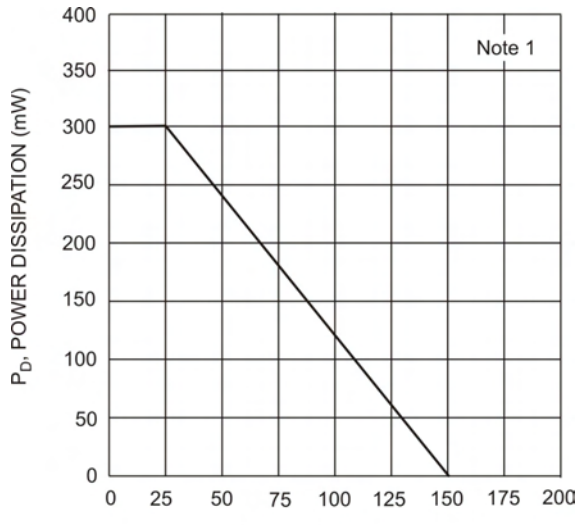


Fig. 1, Max Power Dissipation vs Ambient Temperature

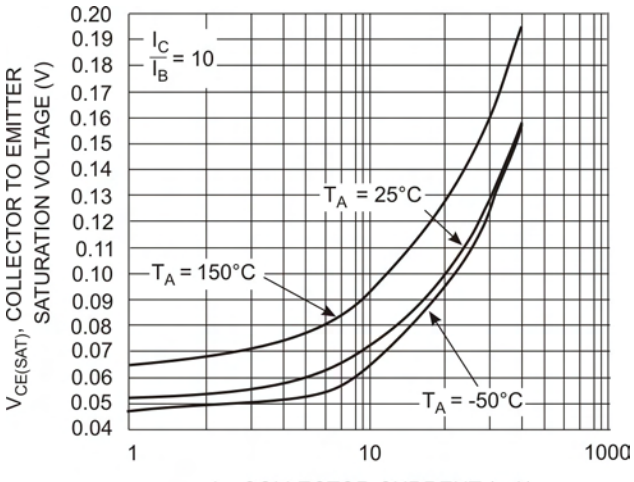


Fig. 2 Collector Emitter Saturation Voltage vs. Collector Current

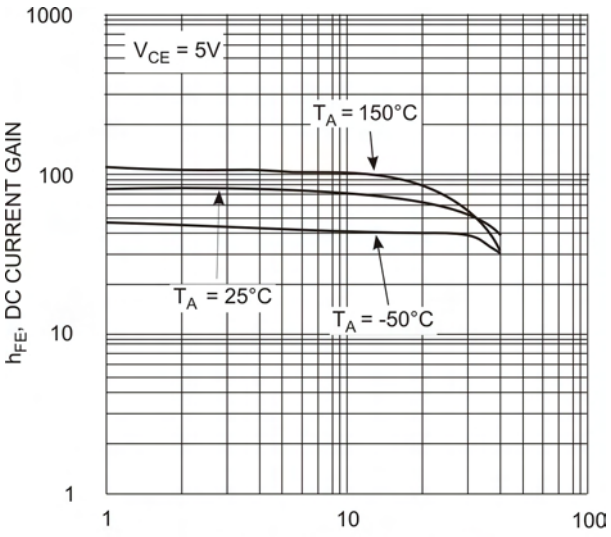


Fig. 3, DC Current Gain vs. Collector Current

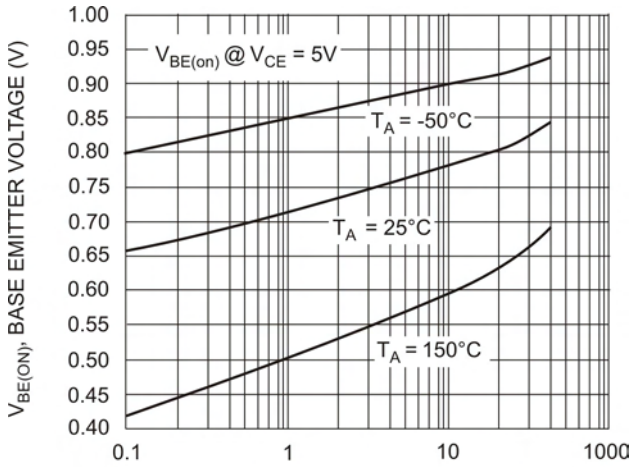


Fig. 4 Base Emitter Voltage vs. Collector Current

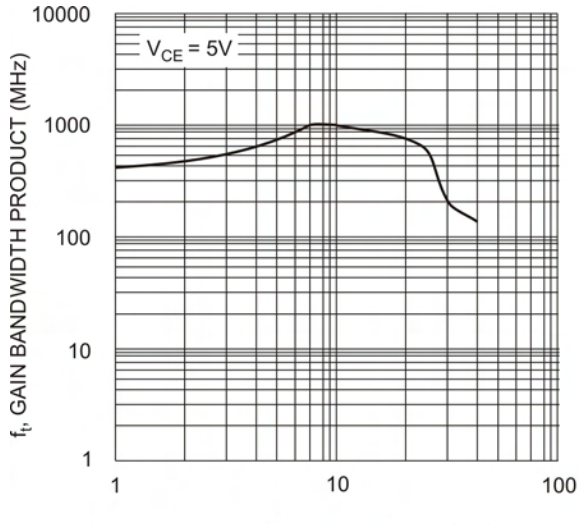


Fig. 5, Gain Bandwidth Product vs Collector Current